

# 74HC2G17-Q100; 74HCT2G17-Q100

## Dual non-inverting Schmitt trigger

Rev. 1 — 22 May 2013

Product data sheet

## 1. General description

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The 74HC2G17-Q100; 74HCT2G17-Q100 are dual buffers with Schmitt-trigger inputs. Inputs include clamp diodes. This enables the use of current limiting resistors to interface inputs to voltages in excess of  $V_{CC}$ . Schmitt trigger inputs transform slowly changing input signals into sharply defined jitter-free output signals.

This product has been qualified to the Automotive Electronics Council (AEC) standard Q100 (Grade 1) and is suitable for use in automotive applications.

## 2. Features and benefits

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- Automotive product qualification in accordance with AEC-Q100 (Grade 1)
  - ◆ Specified from  $-40\text{ }^{\circ}\text{C}$  to  $+85\text{ }^{\circ}\text{C}$  and from  $-40\text{ }^{\circ}\text{C}$  to  $+125\text{ }^{\circ}\text{C}$
- Input levels:
  - ◆ For 74HC2G17-Q100: CMOS level
  - ◆ For 74HCT2G17-Q100: TTL level
- Complies with JEDEC standard no. 7A
- High noise immunity
- ESD protection:
  - ◆ MIL-STD-883, method 3015 exceeds 2000 V
  - ◆ HBM JESD22-A114F exceeds 2000 V
  - ◆ MM JESD22-A115-A exceeds 200 V ( $C = 200\text{ pF}$ ,  $R = 0\text{ }\Omega$ )
- Low power dissipation
- Balanced propagation delays
- Unlimited input rise and fall times
- Multiple package options

## 3. Applications

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- Wave and pulse shaper for highly noisy environments
- Astable multivibrators
- Monostable multivibrators



## 4. Ordering information

Table 1. Ordering information

Type number	Package			Version
	Temperature range	Name	Description	
74HC2G17GW-Q100	-40 °C to +125 °C	SC-88	plastic surface-mounted package; 6 leads	SOT363
74HC2G17GV-Q100	-40 °C to +125 °C	SC-74	plastic surface-mounted package (TSOP6); 6 leads	SOT457
74HCT2G17GW-Q100	-40 °C to +125 °C	SC-88	plastic surface-mounted package; 6 leads	SOT363
74HCT2G17GV-Q100	-40 °C to +125 °C	SC-74	plastic surface-mounted package (TSOP6); 6 leads	SOT457

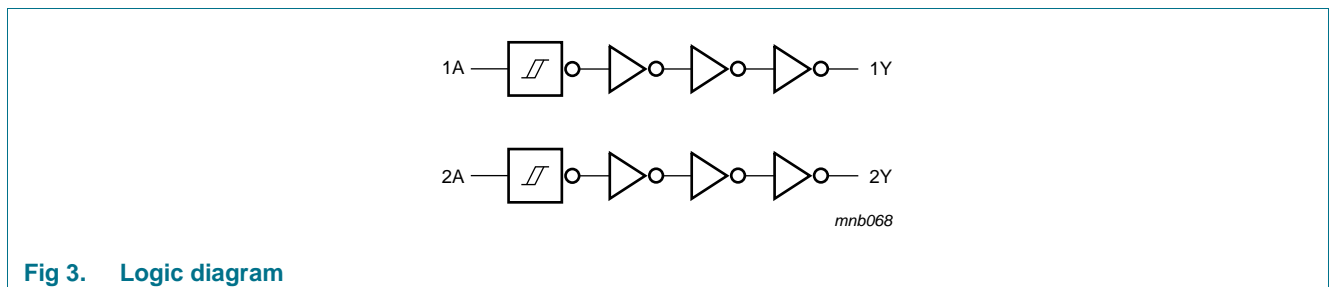
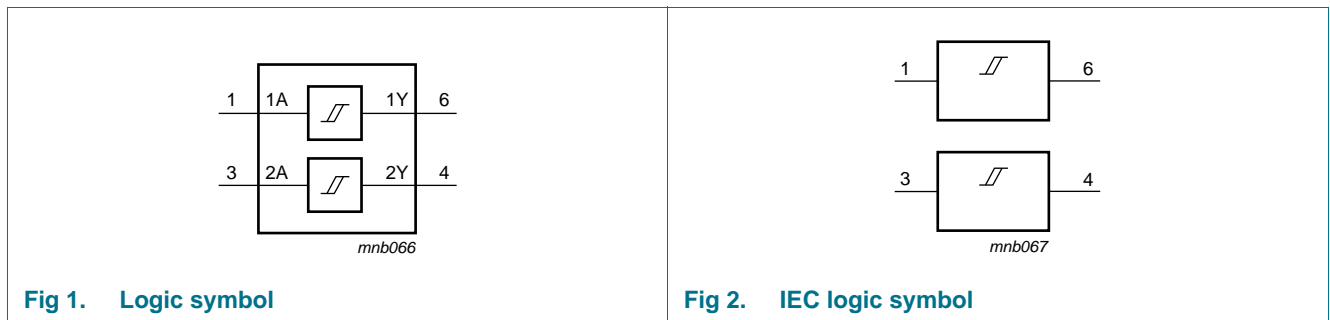
## 5. Marking

Table 2. Marking

Type number	Marking code <sup>[1]</sup>
74HC2G17GW-Q100	HV
74HC2G17GV-Q100	HV
74HCT2G17GW-Q100	TV
74HCT2G17GV-Q100	TV

[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

## 6. Functional diagram



## 7. Pinning information

### 7.1 Pinning

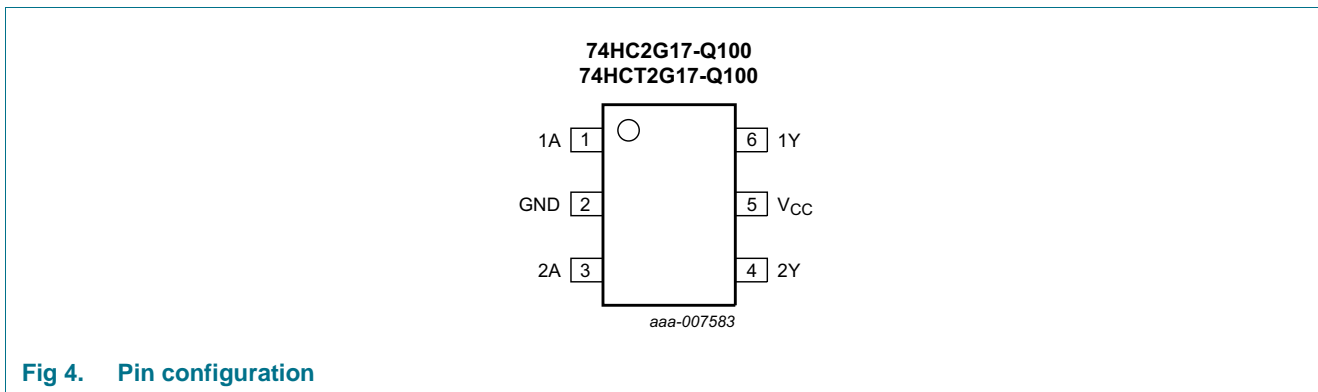


Fig 4. Pin configuration

### 7.2 Pin description

Table 3. Pin description

Symbol	Pin	Description
1A	1	data input
GND	2	ground (0 V)
2A	3	data input
2Y	4	data output
V <sub>CC</sub>	5	supply voltage
1Y	6	data output

## 8. Functional description

Table 4. Function table<sup>[1]</sup>

Input	Output
nA	nY
L	L
H	H

[1] H = HIGH voltage level;  
L = LOW voltage level.

## 9. Limiting values

**Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{CC}$	supply voltage		-0.5	+7.0	V
$I_{IK}$	input clamping current	$V_I < -0.5\text{ V}$ or $V_I > V_{CC} + 0.5\text{ V}$	[1] -	±20	mA
$I_{OK}$	output clamping current	$V_O < -0.5\text{ V}$ or $V_O > V_{CC} + 0.5\text{ V}$	[1] -	±20	mA
$I_O$	output current	$V_O = -0.5\text{ V}$ to $V_{CC} + 0.5\text{ V}$	[1] -	±25	mA
$I_{CC}$	supply current		[1] -	50	mA
$I_{GND}$	ground current		[1] -	-50	mA
$T_{stg}$	storage temperature		-65	+150	°C
$P_{tot}$	total power dissipation		[2] -	250	mW

[1] The minimum input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] For SC-88 and SC-74 packages: above 87.5 °C the value of  $P_{tot}$  derates linearly with 4.0 mW/K.

## 10. Recommended operating conditions

**Table 6. Recommended operating conditions**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>74HC2G17-Q100</b>						
$V_{CC}$	supply voltage		2.0	5.0	6.0	V
$V_I$	input voltage		0	-	$V_{CC}$	V
$V_O$	output voltage		0	-	$V_{CC}$	V
$T_{amb}$	ambient temperature		-40	+25	+125	°C
<b>74HCT2G17-Q100</b>						
$V_{CC}$	supply voltage		4.5	5.0	5.5	V
$V_I$	input voltage		0	-	$V_{CC}$	V
$V_O$	output voltage		0	-	$V_{CC}$	V
$T_{amb}$	ambient temperature		-40	+25	+125	°C

## 11. Static characteristics

**Table 7. Static characteristics for 74HC2G17**

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b><math>T_{amb} = 25\text{ °C}</math></b>						
$V_{OH}$	HIGH-level output voltage	$V_I = V_{T+}$ or $V_{T-}$				
		$I_O = -20\text{ }\mu\text{A}; V_{CC} = 2.0\text{ V}$	1.9	2.0	-	V
		$I_O = -20\text{ }\mu\text{A}; V_{CC} = 4.5\text{ V}$	4.4	4.5	-	V
		$I_O = -20\text{ }\mu\text{A}; V_{CC} = 6.0\text{ V}$	5.9	6.0	-	V
		$I_O = -4.0\text{ mA}; V_{CC} = 4.5\text{ V}$	4.18	4.32	-	V
		$I_O = -5.2\text{ mA}; V_{CC} = 6.0\text{ V}$	5.68	5.81	-	V

**Table 7. Static characteristics for 74HC2G17 ...continued**

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V <sub>OL</sub>	LOW-level output voltage	V <sub>I</sub> = V <sub>T+</sub> or V <sub>T-</sub>				
		I <sub>O</sub> = 20 μA; V <sub>CC</sub> = 2.0 V	-	0	0.1	V
		I <sub>O</sub> = 20 μA; V <sub>CC</sub> = 4.5 V	-	0	0.1	V
		I <sub>O</sub> = 20 μA; V <sub>CC</sub> = 6.0 V	-	0	0.1	V
		I <sub>O</sub> = 4.0 mA; V <sub>CC</sub> = 4.5 V	-	0.15	0.26	V
		I <sub>O</sub> = 5.2 mA; V <sub>CC</sub> = 6.0 V	-	0.16	0.26	V
I <sub>I</sub>	input leakage current	V <sub>I</sub> = GND or V <sub>CC</sub> ; V <sub>CC</sub> = 6.0 V	-	-	±0.1	μA
I <sub>CC</sub>	supply current	V <sub>I</sub> = GND or V <sub>CC</sub> ; I <sub>O</sub> = 0 A; V <sub>CC</sub> = 6.0 V	-	-	1.0	μA
C <sub>I</sub>	input capacitance		-	2.0	-	pF
<b>T<sub>amb</sub> = -40 °C to +85 °C</b>						
V <sub>OH</sub>	HIGH-level output voltage	V <sub>I</sub> = V <sub>T+</sub> or V <sub>T-</sub>				
		I <sub>O</sub> = -20 μA; V <sub>CC</sub> = 2.0 V	1.9	-	-	V
		I <sub>O</sub> = -20 μA; V <sub>CC</sub> = 4.5 V	4.4	-	-	V
		I <sub>O</sub> = -20 μA; V <sub>CC</sub> = 6.0 V	5.9	-	-	V
		I <sub>O</sub> = -4.0 mA; V <sub>CC</sub> = 4.5 V	4.13	-	-	V
		I <sub>O</sub> = -5.2 mA; V <sub>CC</sub> = 6.0 V	5.63	-	-	V
V <sub>OL</sub>	LOW-level output voltage	V <sub>I</sub> = V <sub>T+</sub> or V <sub>T-</sub>				
		I <sub>O</sub> = 20 μA; V <sub>CC</sub> = 2.0 V	-	-	0.1	V
		I <sub>O</sub> = 20 μA; V <sub>CC</sub> = 4.5 V	-	-	0.1	V
		I <sub>O</sub> = 20 μA; V <sub>CC</sub> = 6.0 V	-	-	0.1	V
		I <sub>O</sub> = 4.0 mA; V <sub>CC</sub> = 4.5 V	-	-	0.33	V
		I <sub>O</sub> = 5.2 mA; V <sub>CC</sub> = 6.0 V	-	-	0.33	V
I <sub>I</sub>	input leakage current	V <sub>I</sub> = GND or V <sub>CC</sub> ; V <sub>CC</sub> = 6.0 V	-	-	±1.0	μA
I <sub>CC</sub>	supply current	V <sub>I</sub> = GND or V <sub>CC</sub> ; I <sub>O</sub> = 0 A; V <sub>CC</sub> = 6.0 V	-	-	10.0	μA
<b>T<sub>amb</sub> = -40 °C to +125 °C</b>						
V <sub>OH</sub>	HIGH-level output voltage	V <sub>I</sub> = V <sub>T+</sub> or V <sub>T-</sub>				
		I <sub>O</sub> = -20 μA; V <sub>CC</sub> = 2.0 V	1.9	-	-	V
		I <sub>O</sub> = -20 μA; V <sub>CC</sub> = 4.5 V	4.4	-	-	V
		I <sub>O</sub> = -20 μA; V <sub>CC</sub> = 6.0 V	5.9	-	-	V
		I <sub>O</sub> = -4.0 mA; V <sub>CC</sub> = 4.5 V	3.7	-	-	V
		I <sub>O</sub> = -5.2 mA; V <sub>CC</sub> = 6.0 V	5.2	-	-	V

**Table 7.** Static characteristics for 74HC2G17 ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V <sub>OL</sub>	LOW-level output voltage	V <sub>I</sub> = V <sub>T+</sub> or V <sub>T-</sub>				
		I <sub>O</sub> = 20 μA; V <sub>CC</sub> = 2.0 V	-	-	0.1	V
		I <sub>O</sub> = 20 μA; V <sub>CC</sub> = 4.5 V	-	-	0.1	V
		I <sub>O</sub> = 20 μA; V <sub>CC</sub> = 6.0 V	-	-	0.1	V
		I <sub>O</sub> = 4.0 mA; V <sub>CC</sub> = 4.5 V	-	-	0.4	V
		I <sub>O</sub> = 5.2 mA; V <sub>CC</sub> = 6.0 V	-	-	0.4	V
I <sub>I</sub>	input leakage current	V <sub>I</sub> = GND or V <sub>CC</sub> ; V <sub>CC</sub> = 6.0 V	-	-	±1.0	μA
I <sub>CC</sub>	supply current	V <sub>I</sub> = GND or V <sub>CC</sub> ; I <sub>O</sub> = 0 A; V <sub>CC</sub> = 6.0 V	-	-	20.0	μA

**Table 8.** Static characteristics for 74HCT2G17

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>T<sub>amb</sub> = 25 °C</b>						
V <sub>OH</sub>	HIGH-level output voltage	V <sub>I</sub> = V <sub>T+</sub> or V <sub>T-</sub> ; V <sub>CC</sub> = 4.5 V				
		I <sub>O</sub> = -20 μA	4.4	4.5	-	V
		I <sub>O</sub> = -4.0 mA	4.18	4.32	-	V
V <sub>OL</sub>	LOW-level output voltage	V <sub>I</sub> = V <sub>T+</sub> or V <sub>T-</sub> ; V <sub>CC</sub> = 4.5 V				
		I <sub>O</sub> = -20 μA	-	0	0.1	V
		I <sub>O</sub> = -4.0 mA	-	0.15	0.26	V
I <sub>I</sub>	input leakage current	V <sub>I</sub> = GND or V <sub>CC</sub> ; V <sub>CC</sub> = 5.5 V	-	-	±0.1	μA
I <sub>CC</sub>	supply current	V <sub>I</sub> = GND or V <sub>CC</sub> ; I <sub>O</sub> = 0 A; V <sub>CC</sub> = 5.5 V	-	-	1.0	μA
ΔI <sub>CC</sub>	additional supply current	V <sub>I</sub> = V <sub>CC</sub> - 2.1 V; V <sub>CC</sub> = 4.5 V to 5.5 V; I <sub>O</sub> = 0 A	-	-	300	μA
C <sub>I</sub>	input capacitance		-	2.0	-	pF
<b>T<sub>amb</sub> = -40 °C to +85 °C</b>						
V <sub>OH</sub>	HIGH-level output voltage	V <sub>I</sub> = V <sub>T+</sub> or V <sub>T-</sub> ; V <sub>CC</sub> = 4.5 V				
		I <sub>O</sub> = -20 μA	4.4	-	-	V
		I <sub>O</sub> = -4.0 mA	4.13	-	-	V
V <sub>OL</sub>	LOW-level output voltage	V <sub>I</sub> = V <sub>T+</sub> or V <sub>T-</sub> ; V <sub>CC</sub> = 4.5 V				
		I <sub>O</sub> = -20 μA	-	-	0.1	V
		I <sub>O</sub> = -4.0 mA	-	-	0.33	V
I <sub>I</sub>	input leakage current	V <sub>I</sub> = GND or V <sub>CC</sub> ; V <sub>CC</sub> = 5.5 V	-	-	±1.0	μA
I <sub>CC</sub>	supply current	V <sub>I</sub> = GND or V <sub>CC</sub> ; I <sub>O</sub> = 0 A; V <sub>CC</sub> = 5.5 V	-	-	10.0	μA
ΔI <sub>CC</sub>	additional supply current	V <sub>I</sub> = V <sub>CC</sub> - 2.1 V; V <sub>CC</sub> = 4.5 V to 5.5 V; I <sub>O</sub> = 0 A	-	-	375	μA

**Table 8.** Static characteristics for 74HCT2G17 ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>T<sub>amb</sub> = -40 °C to +125 °C</b>						
V <sub>OH</sub>	HIGH-level output voltage	V <sub>I</sub> = V <sub>T+</sub> or V <sub>T-</sub> ; V <sub>CC</sub> = 4.5 V				
		I <sub>O</sub> = -20 μA	4.4	-	-	V
		I <sub>O</sub> = -4.0 mA	3.7	-	-	V
V <sub>OL</sub>	LOW-level output voltage	V <sub>I</sub> = V <sub>T+</sub> or V <sub>T-</sub> ; V <sub>CC</sub> = 4.5 V				
		I <sub>O</sub> = -20 μA	-	-	0.1	V
		I <sub>O</sub> = -4.0 mA	-	-	0.4	V
I <sub>I</sub>	input leakage current	V <sub>I</sub> = GND or V <sub>CC</sub> ; V <sub>CC</sub> = 5.5 V	-	-	±1.0	μA
I <sub>CC</sub>	supply current	V <sub>I</sub> = GND or V <sub>CC</sub> ; I <sub>O</sub> = 0 A; V <sub>CC</sub> = 5.5 V	-	-	20.0	μA
ΔI <sub>CC</sub>	additional supply current	V <sub>I</sub> = V <sub>CC</sub> - 2.1 V; V <sub>CC</sub> = 4.5 V to 5.5 V; I <sub>O</sub> = 0 A	-	-	410	μA

## 12. Dynamic characteristics

**Table 9.** Dynamic characteristicsVoltages are referenced to GND (ground = 0 V); for test circuit see [Figure 6](#).

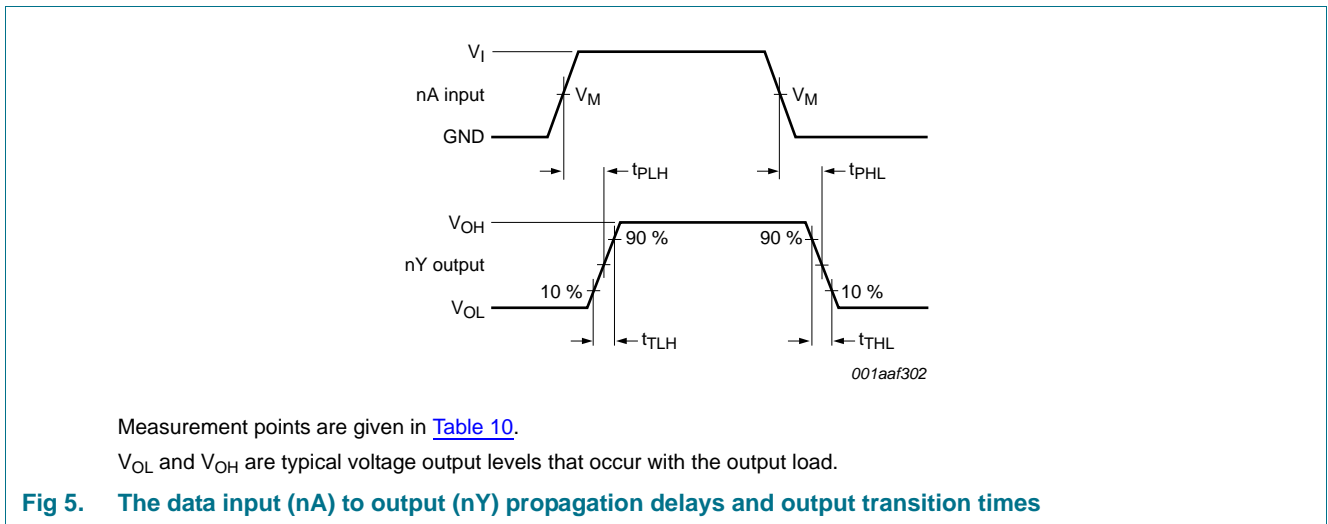
Symbol	Parameter	Conditions	25 °C			-40 °C to +125 °C			Unit
			Min	Typ	Max	Min	Max (85 °C)	Max (125 °C)	
<b>74HC2G17-Q100</b>									
t <sub>pd</sub>	propagation delay	nA to nY; see <a href="#">Figure 5</a> <a href="#">[1]</a>							
		V <sub>CC</sub> = 2.0 V; C <sub>L</sub> = 50 pF	-	36	115	-	140	175	ns
		V <sub>CC</sub> = 4.5 V; C <sub>L</sub> = 50 pF	-	12	22	-	27	34	ns
		V <sub>CC</sub> = 6.0 V; C <sub>L</sub> = 50 pF	-	10	18	-	22	28	ns
t <sub>t</sub>	transition time	nY; see <a href="#">Figure 5</a> <a href="#">[2]</a>							
		V <sub>CC</sub> = 2.0 V; C <sub>L</sub> = 50 pF	-	20	75	-	95	110	ns
		V <sub>CC</sub> = 4.5 V; C <sub>L</sub> = 50 pF	-	7	15	-	19	22	ns
		V <sub>CC</sub> = 6.0 V; C <sub>L</sub> = 50 pF	-	5	13	-	16	19	ns
C <sub>PD</sub>	power dissipation capacitance	V <sub>I</sub> = GND to V <sub>CC</sub> <a href="#">[3]</a>	-	10	-	-	-	-	pF

**Table 9. Dynamic characteristics ...continued**  
 Voltages are referenced to GND (ground = 0 V); for test circuit see [Figure 6](#).

Symbol	Parameter	Conditions	25 °C			-40 °C to +125 °C			Unit
			Min	Typ	Max	Min	Max (85 °C)	Max (125 °C)	
<b>74HCT2G17-Q100</b>									
t <sub>pd</sub>	propagation delay	nA to nY; see <a href="#">Figure 5</a> <a href="#">[1]</a>							
		V <sub>CC</sub> = 4.5 V; C <sub>L</sub> = 50 pF	-	21	29	-	36	45	ns
t <sub>t</sub>	transition time	nY; see <a href="#">Figure 5</a> <a href="#">[2]</a>							
		V <sub>CC</sub> = 4.5 V; C <sub>L</sub> = 50 pF	-	6	15	-	19	22	ns
C <sub>PD</sub>	power dissipation capacitance	V <sub>I</sub> = GND to V <sub>CC</sub> - 1.5 V <a href="#">[3]</a>	-	10	-	-	-	-	pF

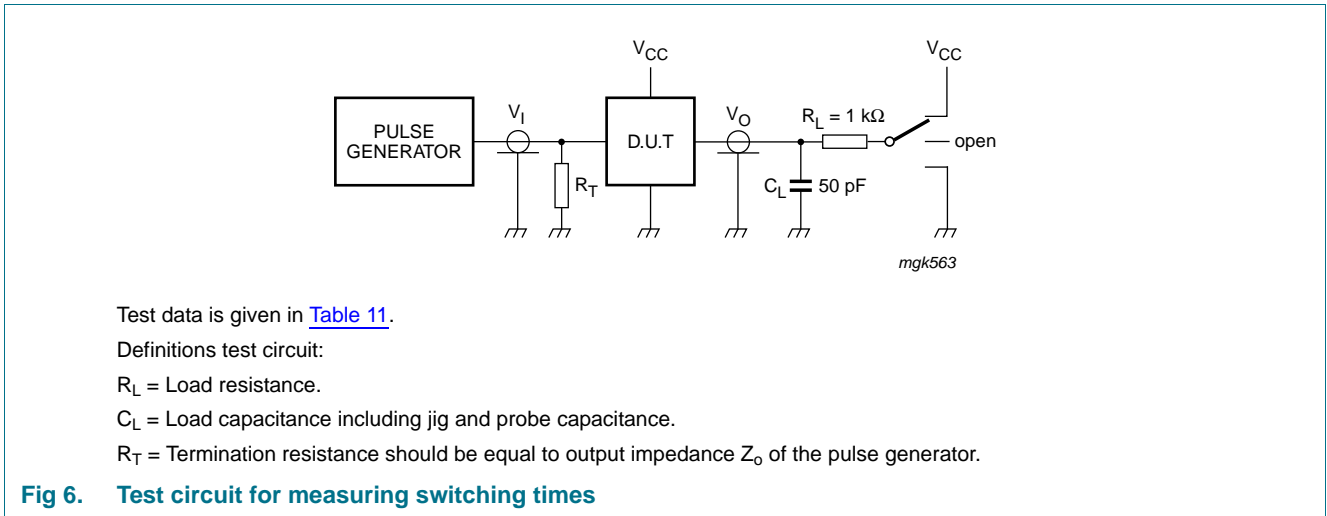
- [1] t<sub>pd</sub> is the same as t<sub>PLH</sub> and t<sub>PHL</sub>
- [2] t<sub>t</sub> is the same as t<sub>TLH</sub> and t<sub>THL</sub>
- [3] C<sub>PD</sub> is used to determine the dynamic power dissipation (P<sub>D</sub> in μW).  
 $P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma(C_L \times V_{CC}^2 \times f_o)$  where:  
 f<sub>i</sub> = input frequency in MHz;  
 f<sub>o</sub> = output frequency in MHz;  
 C<sub>L</sub> = output load capacitance in pF;  
 V<sub>CC</sub> = supply voltage in V;  
 N = number of inputs switching;  
 $\Sigma(C_L \times V_{CC}^2 \times f_o)$  = sum of the outputs.

## 13. Waveforms



**Table 10. Measurement points**

Type	Input			Output
	V <sub>M</sub>	V <sub>I</sub>	t <sub>r</sub> = t <sub>f</sub>	V <sub>M</sub>
74HC2G17-Q100	0.5V <sub>CC</sub>	GND to V <sub>CC</sub>	6.0 ns	0.5V <sub>CC</sub>
74HCT2G17-Q100	1.3 V	GND to 3.0 V	6.0 ns	1.3 V



**Table 11. Test data**

Type	Input		Test
	$V_i$	$t_r, t_f$	$t_{PHL}, t_{PLH}$
74HC2G17-Q100	GND to $V_{CC}$	6 ns	open
74HCT2G17-Q100	GND to 3.0 V	6 ns	open

## 14. Transfer characteristics

**Table 12. Transfer characteristics**

Voltages are referenced to GND (ground = 0 V); for test circuit see [Figure 6](#).

Symbol	Parameter	Conditions	25 °C			-40 °C to +125 °C			Unit
			Min	Typ	Max	Min	Max (85 °C)	Max (125 °C)	

### 74HC2G17-Q100

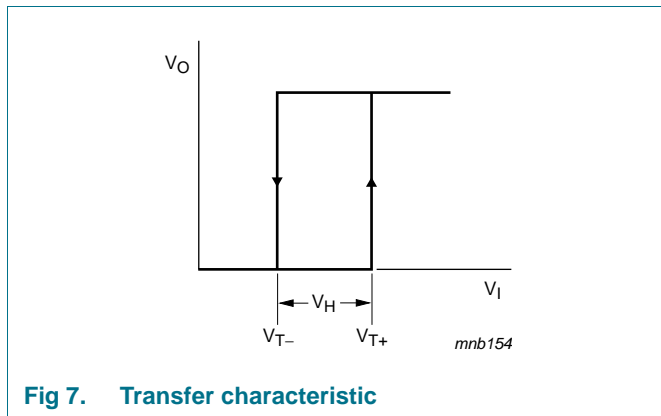
$V_{T+}$	positive-going threshold voltage	see <a href="#">Figure 7</a> , <a href="#">Figure 8</a>							
		$V_{CC} = 2.0\text{ V}$	1.00	1.18	1.50	1.00	1.50	1.50	V
		$V_{CC} = 4.5\text{ V}$	2.30	2.60	3.15	2.30	3.15	3.15	V
$V_{T-}$	negative-going threshold voltage	$V_{CC} = 6.0\text{ V}$	3.00	3.46	4.20	3.00	4.20	4.20	V
		see <a href="#">Figure 7</a> , <a href="#">Figure 8</a>							
		$V_{CC} = 2.0\text{ V}$	0.30	0.60	0.90	0.30	0.90	0.90	V
$V_H$	hysteresis voltage	$V_{CC} = 4.5\text{ V}$	1.13	1.47	2.00	1.13	2.00	2.00	V
		$V_{CC} = 6.0\text{ V}$	1.50	2.06	2.60	1.50	2.60	2.60	V
		$V_{T+} - V_{T-}$ ; see <a href="#">Figure 7</a> , <a href="#">Figure 8</a> and <a href="#">Figure 9</a>							
$V_H$	hysteresis voltage	$V_{CC} = 2.0\text{ V}$	0.30	0.60	1.00	0.30	1.00	1.00	V
		$V_{CC} = 4.5\text{ V}$	0.60	1.13	1.40	0.60	1.40	1.40	V
		$V_{CC} = 6.0\text{ V}$	0.80	1.40	1.70	0.80	1.70	1.70	V

**Table 12. Transfer characteristics ...continued**

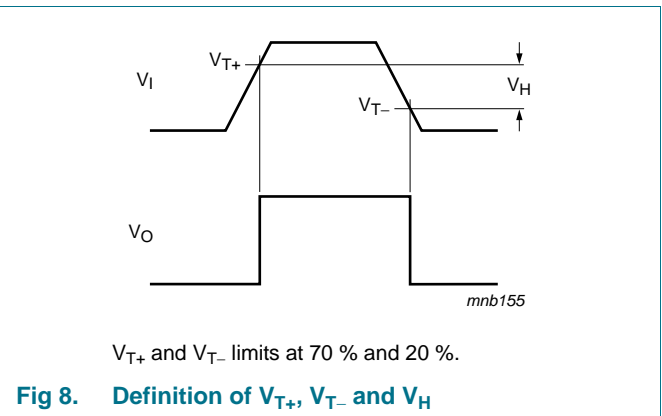
Voltages are referenced to GND (ground = 0 V); for test circuit see [Figure 6](#).

Symbol	Parameter	Conditions	25 °C			-40 °C to +125 °C			Unit
			Min	Typ	Max	Min	Max (85 °C)	Max (125 °C)	
<b>74HCT2G17-Q100</b>									
$V_{T+}$	positive-going threshold voltage	see <a href="#">Figure 7</a> and <a href="#">Figure 8</a>							
		$V_{CC} = 4.5\text{ V}$	1.20	1.58	1.90	1.20	1.90	1.90	V
		$V_{CC} = 5.5\text{ V}$	1.40	1.78	2.10	1.40	2.10	2.10	V
$V_{T-}$	negative-going threshold voltage	see <a href="#">Figure 7</a> and <a href="#">Figure 8</a>							
		$V_{CC} = 4.5\text{ V}$	0.50	0.87	1.20	0.50	1.20	1.20	V
		$V_{CC} = 5.5\text{ V}$	0.60	1.11	1.40	0.60	1.40	1.40	V
$V_H$	hysteresis voltage	$V_{T+} - V_{T-}$ ; see <a href="#">Figure 7</a> , <a href="#">Figure 8</a> and <a href="#">Figure 10</a>							
		$V_{CC} = 4.5\text{ V}$	0.40	0.71	-	0.40	-	-	V
		$V_{CC} = 5.5\text{ V}$	0.40	0.67	-	0.40	-	-	V

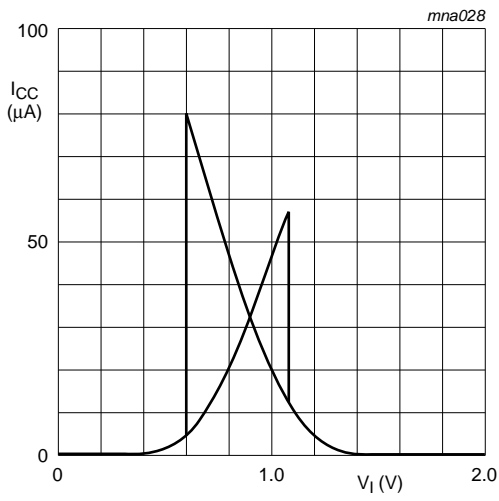
## 15. Waveforms transfer characteristics



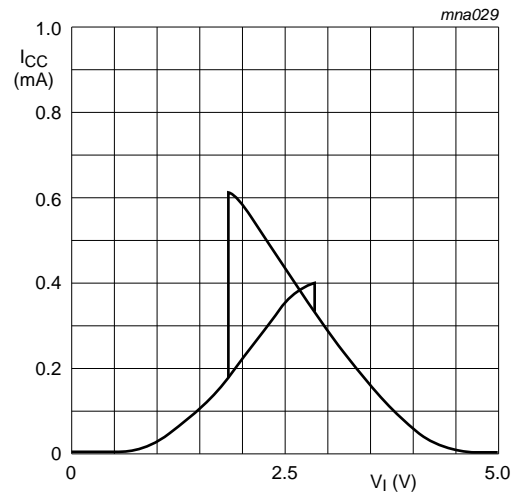
**Fig 7. Transfer characteristic**



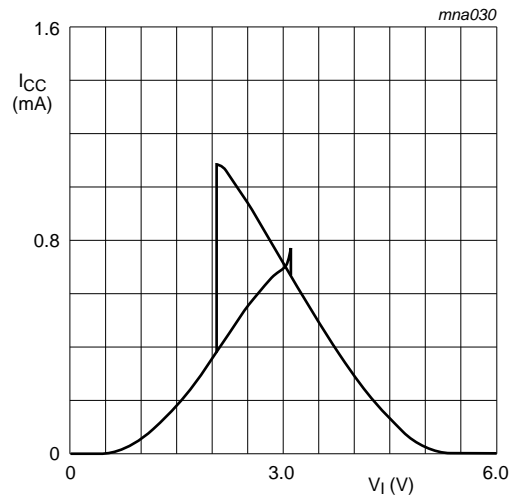
**Fig 8. Definition of  $V_{T+}$ ,  $V_{T-}$  and  $V_H$**



a.  $V_{CC} = 2.0\text{ V}$

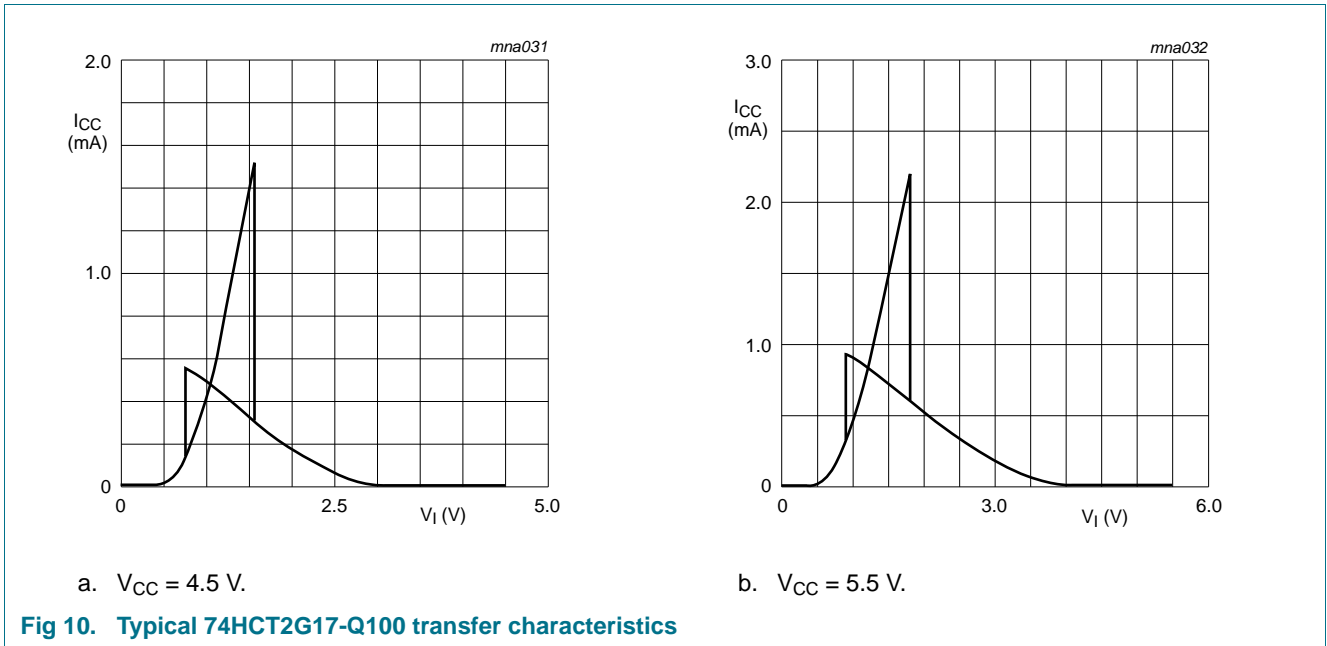


b.  $V_{CC} = 4.5\text{ V}$



c.  $V_{CC} = 6.0\text{ V}$

**Fig 9. Typical 74HC2G17 transfer characteristics**



## 16. Application information

The slow input rise and fall times cause additional power dissipation which can be calculated using the following formula:

$$P_{\text{add}} = f_i \times (t_r \times \Delta I_{\text{CC(AV)}} + t_f \times \Delta I_{\text{CC(AV)}}) \times V_{\text{CC}} \text{ where:}$$

$P_{\text{add}}$  = additional power dissipation ( $\mu\text{W}$ );

$f_i$  = input frequency (MHz);

$t_r$  = input rise time (ns); 10 % to 90 %;

$t_f$  = input fall time (ns); 90 % to 10 %;

$\Delta I_{\text{CC(AV)}}$  = average additional supply current ( $\mu\text{A}$ ).

$\Delta I_{\text{CC(AV)}}$  differs with positive or negative input transitions, as shown in [Figure 11](#) and [Figure 12](#).

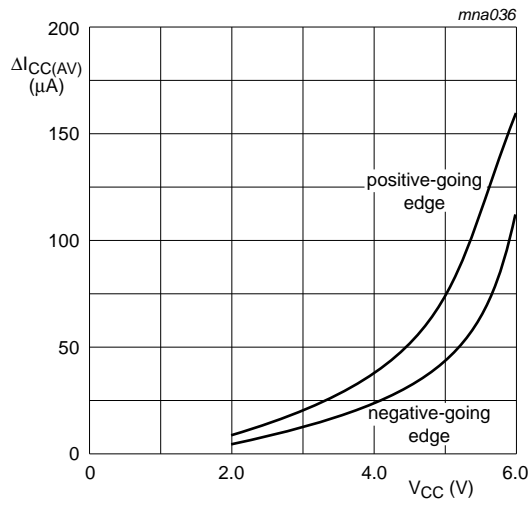


Fig 11.  $\Delta I_{CC(AV)}$  as a function of  $V_{CC}$  for 74HC2G17-Q100; linear change of  $V_I$  between  $0.1V_{CC}$  to  $0.9V_{CC}$

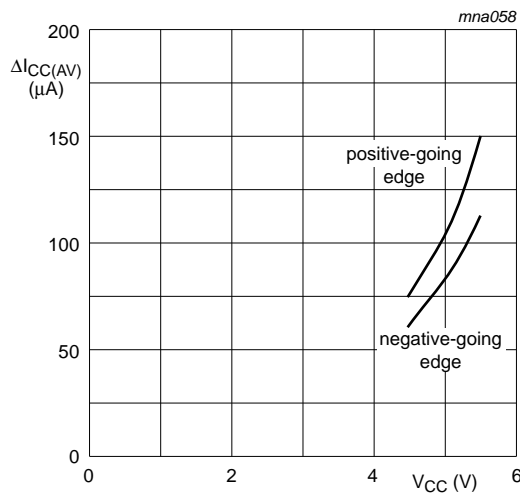


Fig 12.  $\Delta I_{CC(AV)}$  as a function of  $V_{CC}$  for 74HCT2G17-Q100; linear change of  $V_I$  between  $0.1V_{CC}$  to  $0.9V_{CC}$

17. Package outline

Plastic surface-mounted package; 6 leads

SOT363

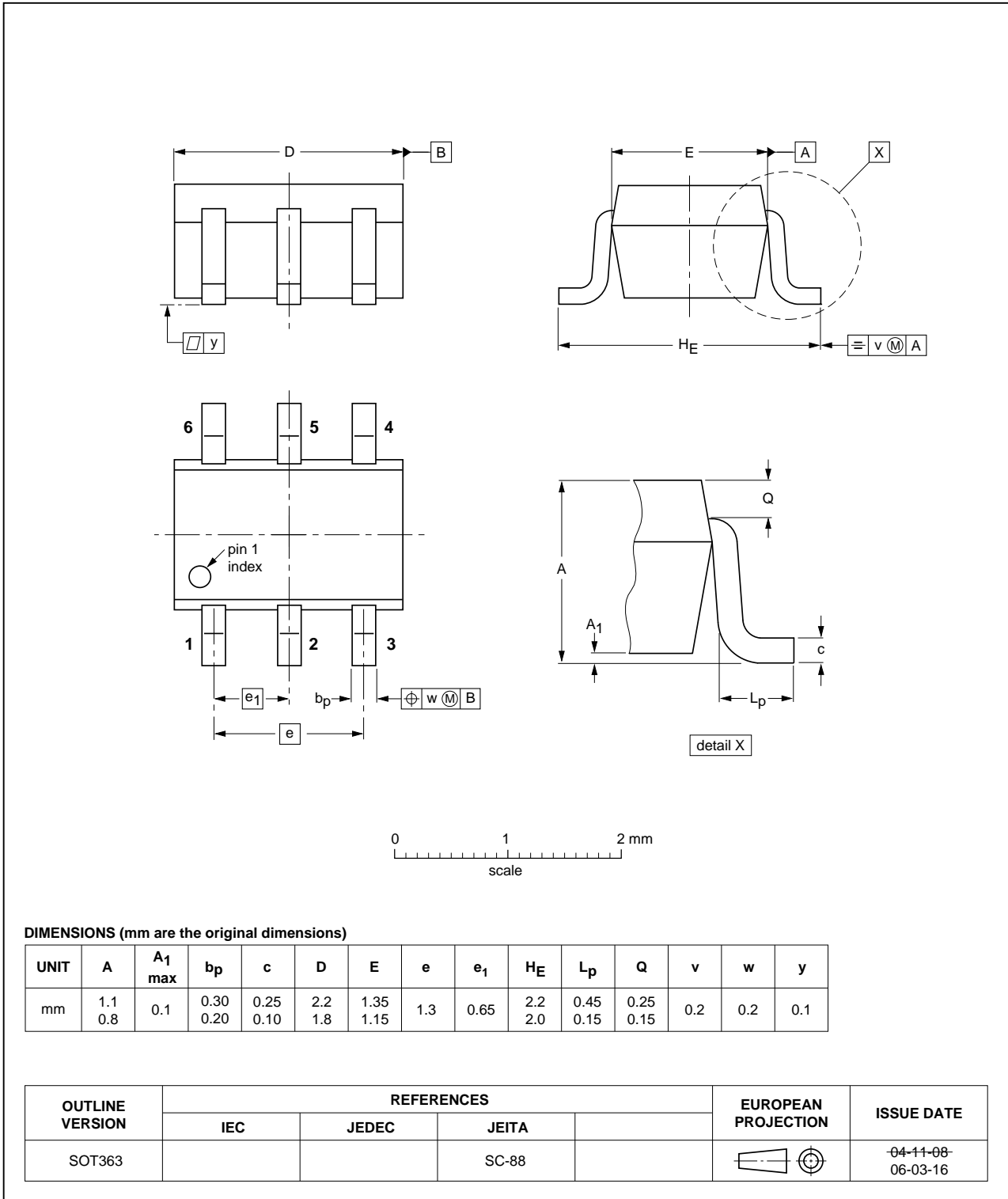


Fig 13. Package outline SOT363 (SC-88)

Plastic surface-mounted package (TSOP6); 6 leads

SOT457

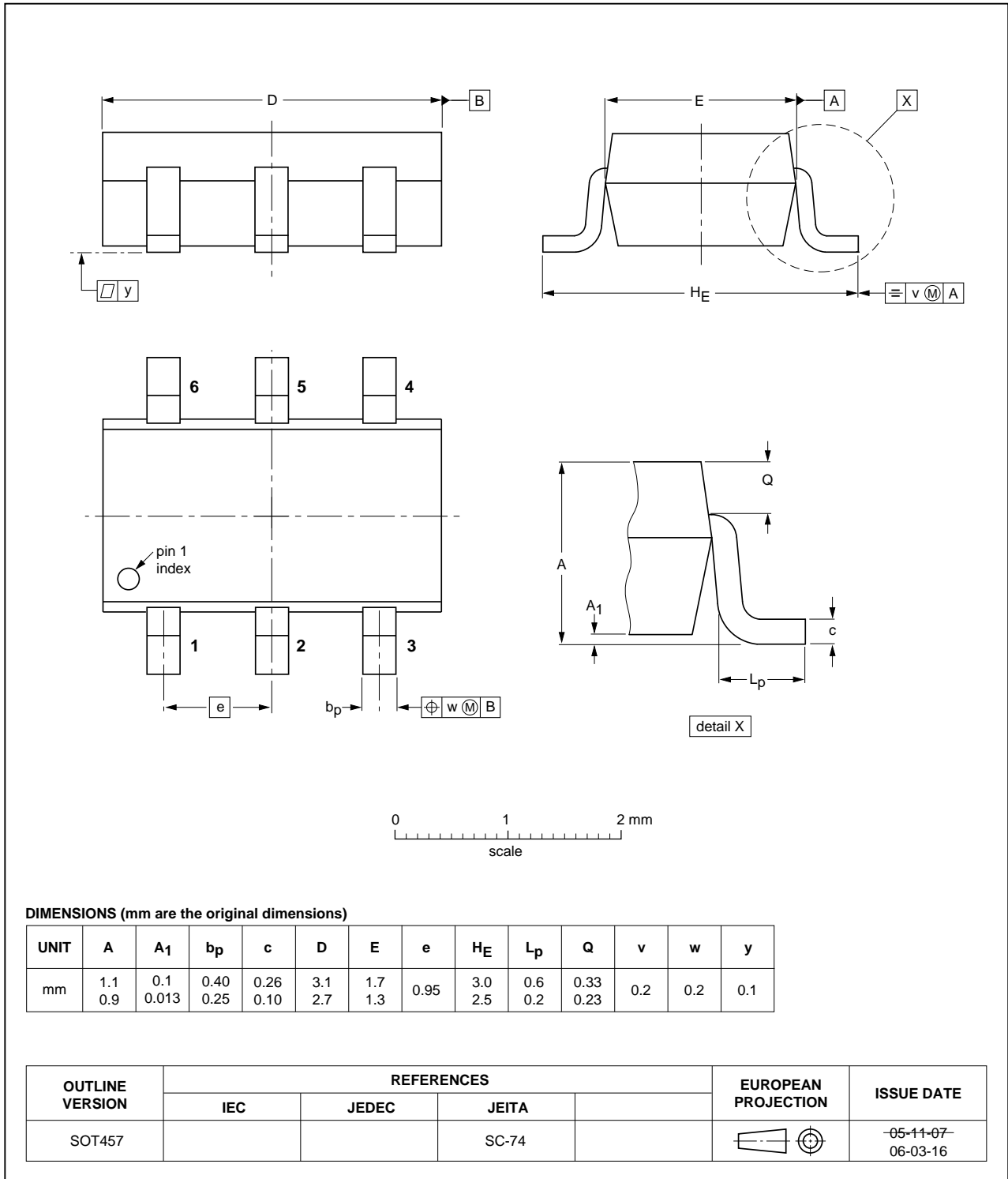


Fig 14. Package outline SOT457 (SC-74)

## 18. Abbreviations

**Table 13. Abbreviations**

Acronym	Description
CMOS	Complementary Metal Oxide Semiconductor
TTL	Transistor-Transistor Logic
HBM	Human Body Model
ESD	ElectroStatic Discharge
MM	Machine Model
DUT	Device Under Test
MIL	Military

## 19. Revision history

**Table 14. Revision history**

Document ID	Release date	Data sheet status	Change notice	Supersedes
74HC_HCT2G17_Q100 v.1	20130522	Product data sheet	-	-

## 20. Legal information

### 20.1 Data sheet status

Document status <sup>[1][2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

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